## SPICE Device Model SiHP22N65E



**Vishay Siliconix** 

# **E Series Power MOSFET**

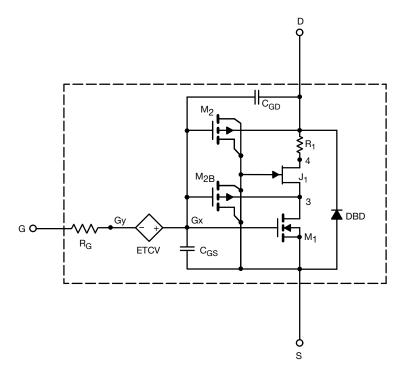
#### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over 25 °C to 150 °C temperature ranges under the pulsed 0 V to 15 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}\xspace$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### **CHARACTERISTICS**

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over 25 °C to 150 °C temperature range
- · Model the gate charge



### SUBCIRCUIT MODEL SCHEMATIC

#### Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |   |                   |                  |      |
|--|---------------------|---|-------------------|------------------|------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS   | SIMULATED<br>DATA | MEASURED<br>DATA | UNIT |
| Static   |                     |   |                   |                  |      |
| Gate-Source Threshold Voltage  | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$   | 3                 | -                | V    |
| Drain-Source On-State Resistance                                       | R <sub>DS(on)</sub> | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$   | 0.16              | 0.15             | Ω    |
| Forward Transconductance   | 9 <sub>fs</sub>     | $V_{DS} = 8 V, I_{D} = 5 A$   | 6.7               | 6.7              | S    |
| Dynamic  |                     |   |                   |                  |      |
| Input Capacitance  | C <sub>iss</sub>    | $V_{DS}$ = 100 V, $V_{GS}$ = 0 V, f = 1 MHz   | 2570              | 2415             | pF   |
| Output Capacitance   | Coss                |   | 200               | 118              |      |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |   | 20                | 4                |      |
| Total Gate Charge  | Qg                  | $V_{DS} = 520 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$                           | 69                | 73               | nC   |
| Gate-Source Charge   | Q <sub>gs</sub>     |   | 15                | 15               |      |
| Gate-Drain Charge  | Q <sub>gd</sub>     |   | 32                | 32               |      |
| Drain-Source Body Diode Characteristics                                |                     |   |                   |                  |      |
| Diode Forward Voltage  | V <sub>SD</sub>     | $T_{J} = 25 \ ^{\circ}C, I_{S} = 11 \ A, V_{GS} = 0 \ V$                                      | 0.91              | -                | V    |
| Reverse Recovery Time  | t <sub>rr</sub>     | $T_J = 25 \text{ °C}, I_F = I_S = 11 \text{ A}, $<br>dI/dt = 100 A/µs, V <sub>R</sub> = 400 V | 400               | 400              | ns   |
| Reverse Recovery Charge  | Q <sub>rr</sub>     |   | 7.8               | 7.3              | μC   |



T<sub>J</sub> = 25 °C

10

15

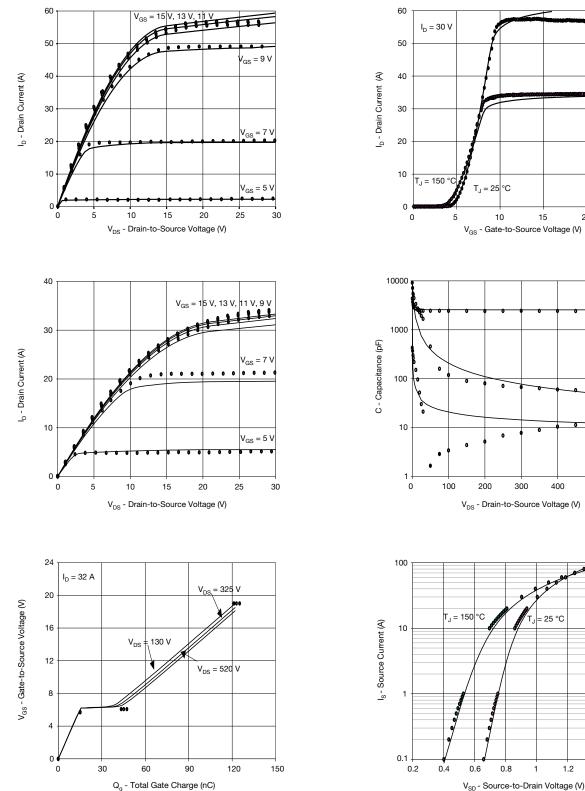
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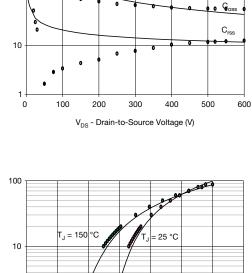
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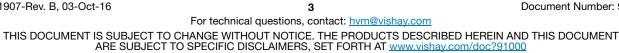
### COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)





0.8

1



· Dots and squares represent measured data.

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1.4

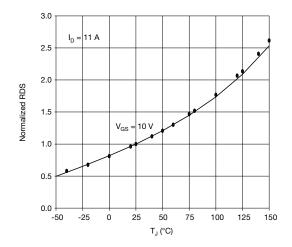
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### **COMPARISON OF MODEL WITH MEASURED DATA** (T<sub>J</sub> = 25 °C, unless otherwise noted)



Note

Dots and squares represent measured data.

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